

Product Summary

BV_{DSS}	$R_{DS(ON)}$ Max	I_D Max $T_C = +25^\circ C$
30V	11m Ω @ $V_{GS} = 10V$	50A
	13m Ω @ $V_{GS} = 4.5V$	45A

Description and Applications

This MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Backlighting
- Power Management Functions
- DC-DC Converters

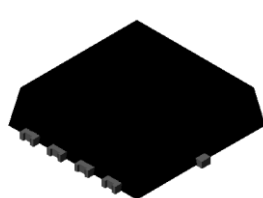
Features and Benefits

- Low $R_{DS(ON)}$ – Ensures On State Losses Are Minimized
- Small Form Factor Thermally Efficient Package Enables Higher Density End Products
- Occupies Just 33% of The Board Area Occupied by SO-8 Enabling Smaller End Product
- Wettable Flank for Improved Optical Inspection
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **An Automotive-Compliant Part is Available Under Separate Datasheet ([DMT3009LFVWQ](#))**

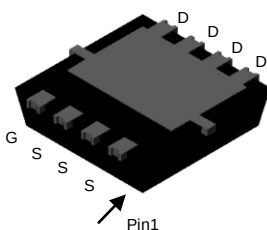
Mechanical Data

- Case: PowerDI[®] 3333-8 (SWP) (Type UX)
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish — Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 
- Weight: 0.03 grams (Approximate)

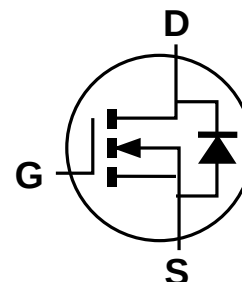
PowerDI3333-8 (SWP) (Type UX)



Top View



Bottom View



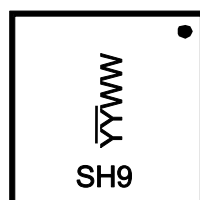
Equivalent Circuit

Ordering Information (Note 4)

Part Number	Case	Packaging
DMT3009LFVW-7	PowerDI3333-8 (SWP) (Type UX)	2,000/Tape & Reel
DMT3009LFVW-13	PowerDI3333-8 (SWP) (Type UX)	3,000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
 2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information



SH9= Product Type Marking Code
 YYWW = Date Code Marking
 YY = Last Two Digits of Year (ex: 18 = 2018)
 WW = Week Code (01 to 53)

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V _{DSS}	30	V
Gate-Source Voltage	V _{GSS}	±20	V
Continuous Drain Current V _{GS} = 10V	I _D	12	A
		10	A
	I _D	50	A
		37	A
Maximum Continuous Body Diode Forward Current (Note 5)	I _S	3	A
Pulsed Drain Current (10μs Pulse, Duty Cycle = 1%)	I _{DM}	90	A
Pulsed Body Diode Forward Current (10μs Pulse, Duty Cycle = 1%)	I _{SM}	90	A
Avalanche Current, L = 0.1mH	I _{AS}	19	A
Avalanche Energy, L = 0.1mH	E _{AS}	19	mJ

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P _D	2.3	W
Thermal Resistance, Junction to Ambient (Note 5)	R _{θJA}	55	°C/W
Total Power Dissipation (Note 8)	P _D	35.7	W
Thermal Resistance, Junction to Case (Note 8)	R _{θJC}	3.5	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)						
Drain-Source Breakdown Voltage	BV _{DSS}	30	-	-	V	V _{GS} = 0V, I _D = 250μA
Zero Gate Voltage Drain Current	I _{DSS}	-	-	1	μA	V _{DS} = 24V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	-	-	±100	nA	V _{GS} = ±16V, V _{DS} = 0V
ON CHARACTERISTICS (Note 6)						
Gate Threshold Voltage	V _{GS(TH)}	1	-	3	V	V _{DS} = V _{GS} , I _D = 250μA
Static Drain-Source On-Resistance	R _{DS(ON)}	-	6.6	11	mΩ	V _{GS} = 10V, I _D = 14.4A
		-	10.5	13		V _{GS} = 4.5V, I _D = 7A
		-	13.4	20		V _{GS} = 3.8V, I _D = 5A
		-	0.8	1.2		V _{GS} = 0V, I _S = 10A
Diode Forward Voltage	V _{SD}	-	0.8	1.2	V	V _{GS} = 0V, I _S = 10A
DYNAMIC CHARACTERISTICS (Note 7)						
Input Capacitance	C _{ISS}	-	823	-	pF	V _{DS} = 15V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	C _{OSS}	-	352	-	pF	
Reverse Transfer Capacitance	C _{RSS}	-	52	-	pF	
Gate Resistance	R _g	-	1.2	-	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1.0MHz
Total Gate Charge (V _{GS} = 4.5V)	Q _g	-	5.8	-	nC	V _{DS} = 15V, I _D = 14.4A
Total Gate Charge (V _{GS} = 10V)	Q _g	-	12	-	nC	
Gate-Source Charge	Q _{gs}	-	1.7	-	nC	
Gate-Drain Charge	Q _{gd}	-	2.4	-	nC	
Turn-On Delay Time	t _{D(ON)}	-	3.2	-	ns	
Turn-On Rise Time	t _r	-	5.2	-	ns	V _{GS} = 10V, V _{DD} = 15V, R _G = 1Ω, I _D = 10A
Turn-Off Delay Time	t _{D(OFF)}	-	8.9	-	ns	
Turn-Off Fall Time	t _f	-	1.5	-	ns	
Body Diode Reverse Recovery Time	t _{RR}	-	16.4	-	ns	I _F = 10A, dI/dt = 100A/μs
Body Diode Reverse Recovery Charge	Q _{RR}	-	5.9	-	nC	

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to product testing.
 - Thermal resistance from junction to soldering point (on the exposed drain pad).

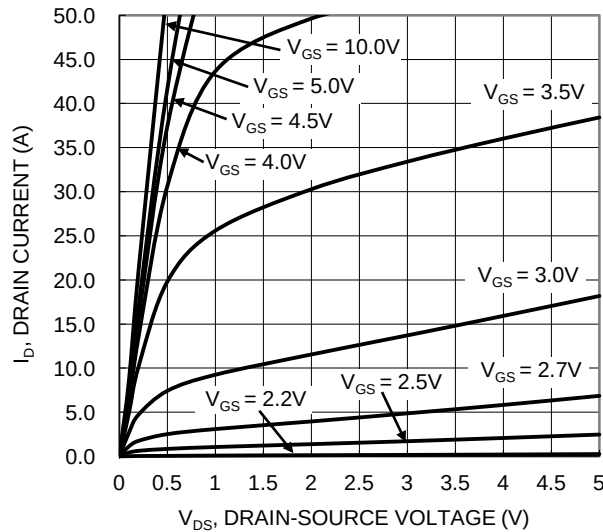


Figure 1. Typical Output Characteristic

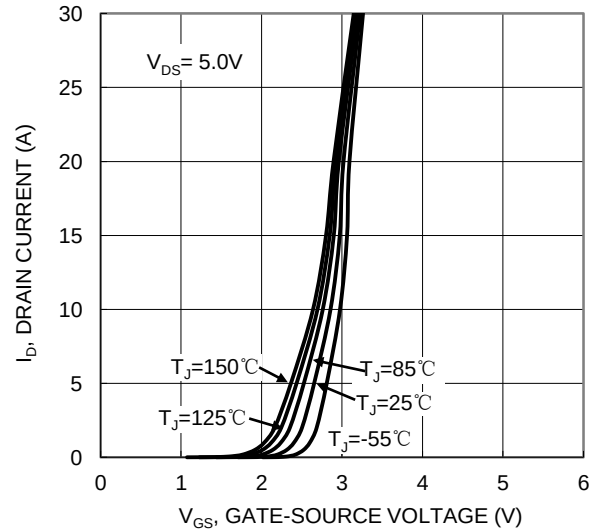


Figure 2. Typical Transfer Characteristic

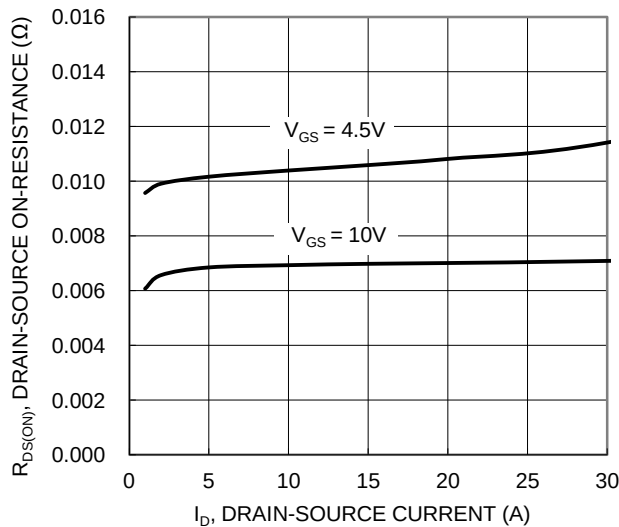


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

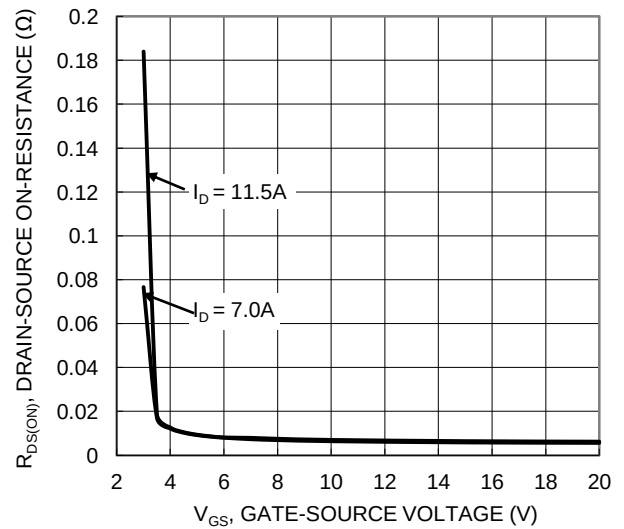


Figure 4. Typical Transfer Characteristic

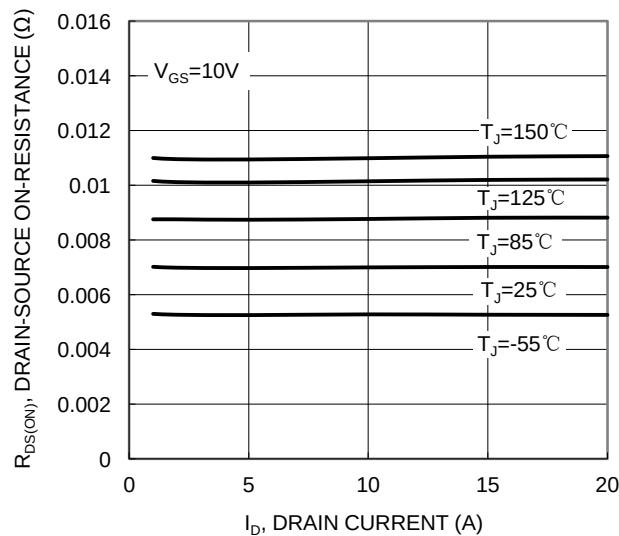


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

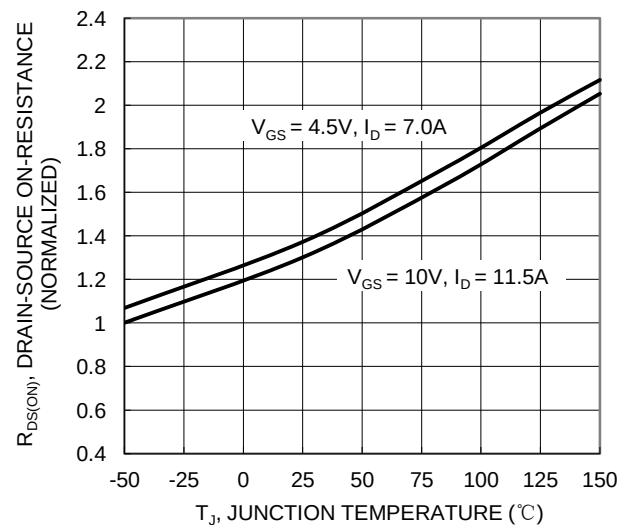
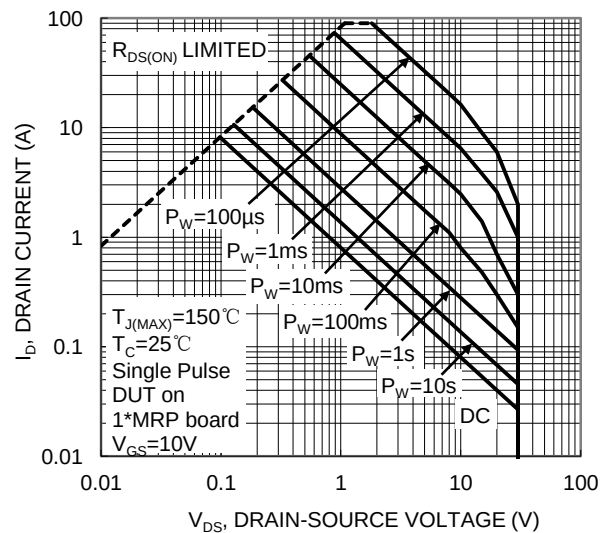
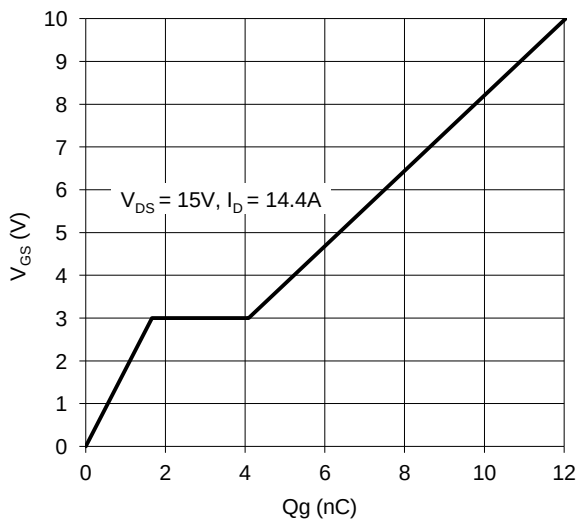
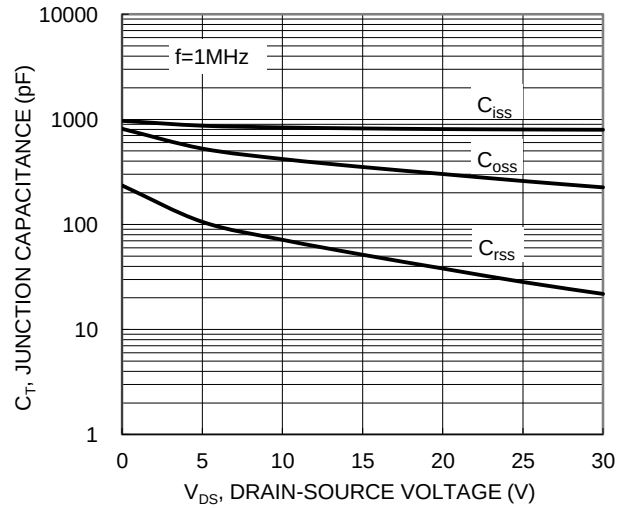
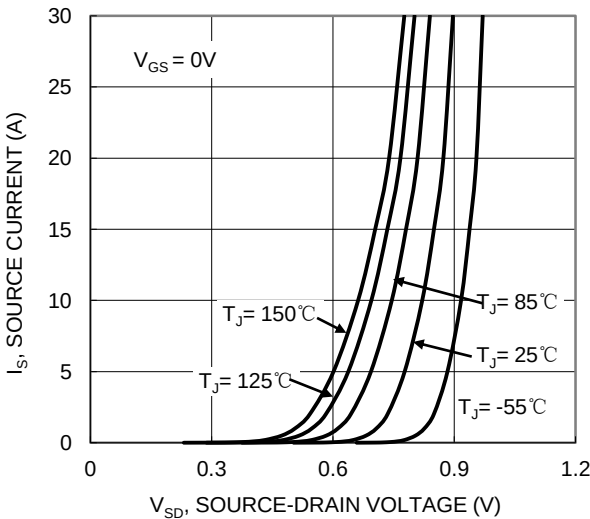
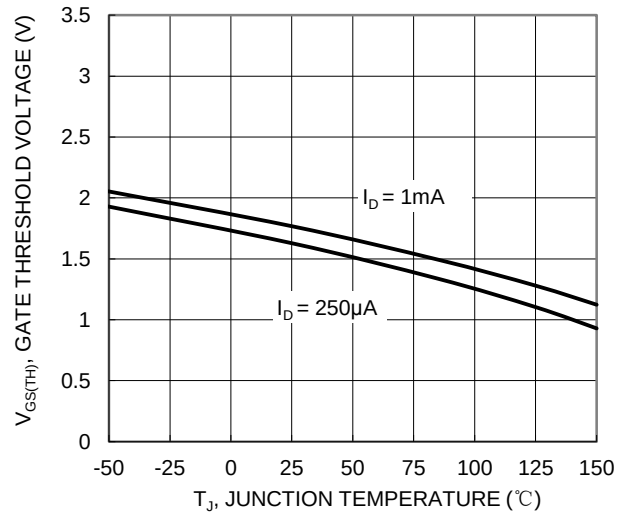
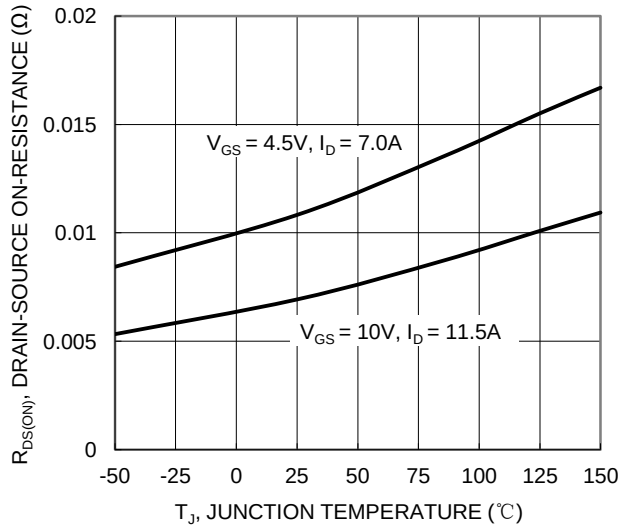


Figure 6. On-Resistance Variation with Temperature



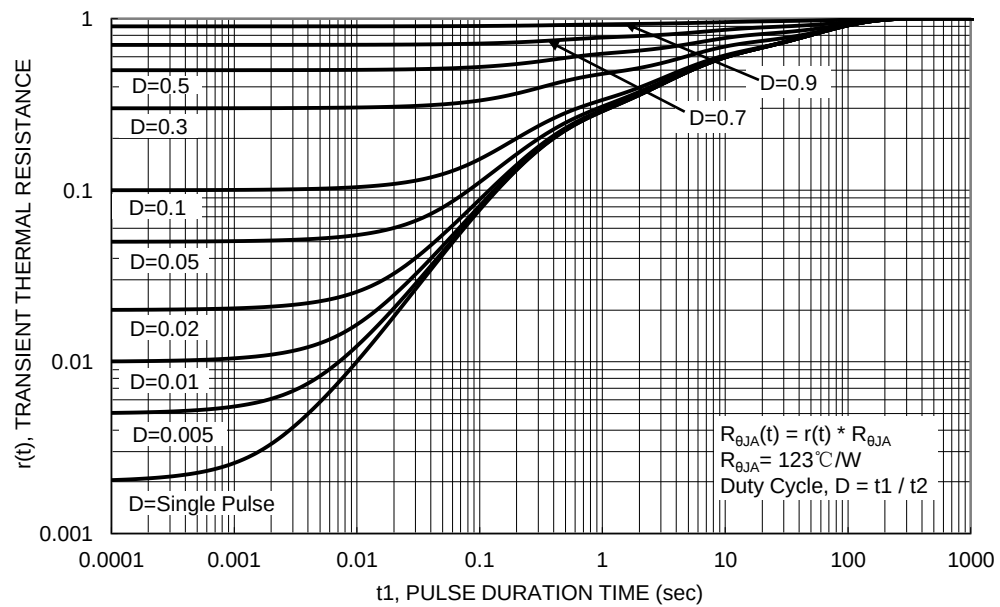
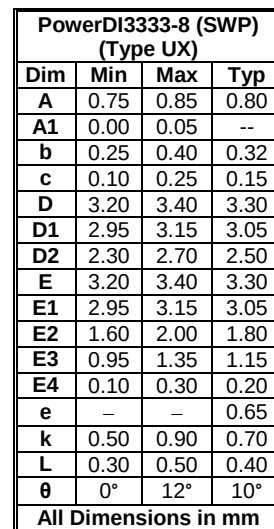


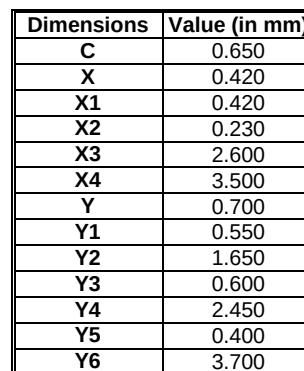
Figure 13. Transient Thermal Resistance

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

PowerDI3333-8 (SWP) (Type UX)

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PowerDI3333-8 (SWP) (Type UX)



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